Low-Voltage CMOS Quad 2-Input XOR Gate

With 5 V-Tolerant Inputs

The MC74LCX86 is a high performance, quad 2–input XOR gate operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX86 inputs to be safely driven from 5.0 V devices.

Current drive capability is 24 mA at the outputs.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Inputs Interface Capability With 5.0 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V

Machine Model >200 V

• Pb-Free Packages are Available*

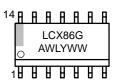


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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A

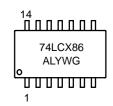




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

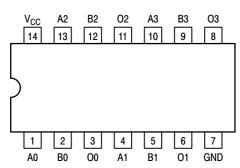


Figure 1. Pinout: 14-Lead (Top View)

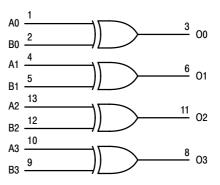


Figure 2. Logic Diagram

PIN NAMES

Pins	Function
An, Bn	Data Inputs
On	Outputs

TRUTH TABLE

Inp	uts	Outputs
An Bn		On
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le V_{CC} + 0.5$	Note 1	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
Vcc	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
V _O	Output Voltage (HIGH or LOW State)	0		V _{CC}	V
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0 V - 3.6 V			-24	mA
I _{OL}	LOW Level Output Current, V _{CC} = 3.0 V - 3.6 V			24	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.7 V - 3.0 V			-12	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.7 V - 3.0 V			12	mA
T _A	Operating Free–Air Temperature	-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			$T_A = -40^{\circ}C$ to $+85^{\circ}C$		
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		V
V _{IL}	LOW Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	V
V _{OH}	HIGH Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V _{CC} – 0.2		V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
II	Input Leakage Current	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5.0	μΑ
I _{CC}	Quiescent Supply Current	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ V}_{I} = \text{GND or V}_{CC}$		10	μΑ
		$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 3.6 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{V}_{IH} = \text{V}_{CC} - 0.6 \text{ V}$		500	μΑ

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS ($t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 \Omega$)

				Limits		
			TA	\ = -40°C to +	+85°C	
			V _{CC} = 3.0	V to 3.6 V	V _{CC} = 2.7 V	
Symbol	Parameter	Waveform	Min	Max	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1,2	1.5 1.5	6.5 6.5	7.0 7.0	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0		ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

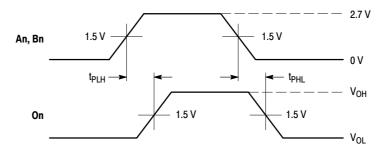
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	7	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF

ORDERING INFORMATION

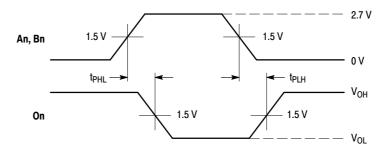
Device	Package	Shipping [†]
MC74LCX86DR2	SOIC-14	2500 Tape & Reel
MC74LCX86DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74LCX86DTR2	TSSOP-14*	2500 Tape & Reel
MC74LCX86DTR2G	TSSOP-14*	2500 Tape & Reel
MC74LCX86M	SOEIAJ-14	50 Units / Rail
MC74LCX86MG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74LCX86MEL	SOEIAJ-14	2000 Tape & Reel
MC74LCX86MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.



WAVEFORM 1 - NON-INVERTING PROPAGATION DELAYS

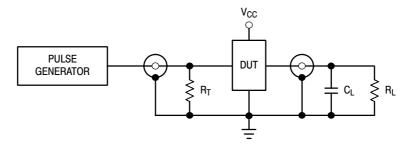
 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns



WAVEFORM 2 - INVERTING PROPAGATION DELAYS

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. AC Waveforms

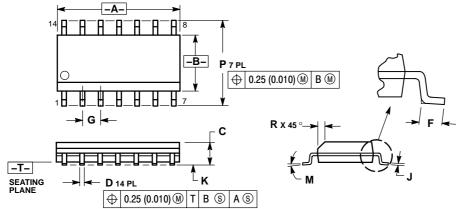


 C_L = 50pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$

Figure 4. Test Circuit

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE G



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

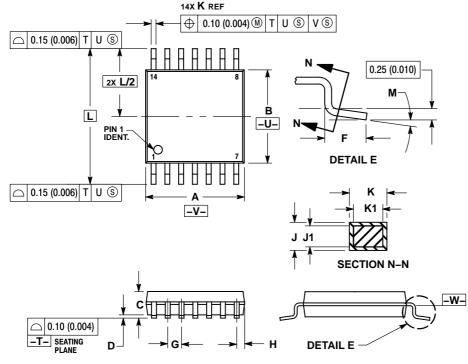
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0°	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



NOTES:

- DTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE
- DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

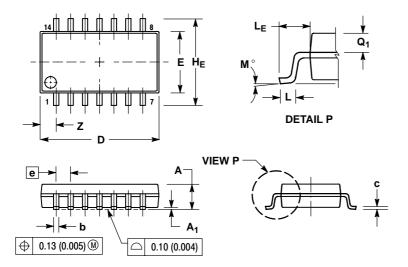
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
M	0°	8 °	0°	8 °	

PACKAGE DIMENSIONS

SOEIAJ-14 M SUFFIX CASE 965-01 ISSUE O



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS O AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROT
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
 PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADIUS OR THE FOOT MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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